ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9
TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: office@roithner-laser.com http://www.roithner-laser.com

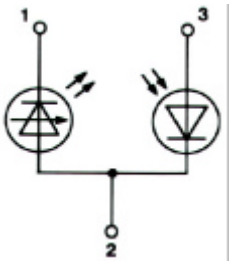
RLT904-20G TECHNICAL DATA

High Power Infrared Laserdiode

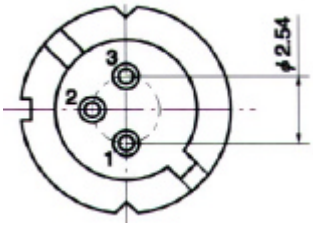
NOTE!
LASERDIODE
MUST BE COOLED!

Structure: **GaAlAs double heterostructure**
Lasing wavelength: **904 nm typ., singlemode**
Max. optical power: **20 mW**
Package: **9 mm**

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	25	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operating Temperature	T_C	-60 .. +60	°C
Storage Temperature	T_{STG}	-70 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}	cw	120	140	160	mA
Operation Current	I_{op}	P_o = 20 mW		175	190	mA
Operation Voltage	U_{op}	P_o = 20 mW		2.2		V
Lasing Wavelength	λ_p	P_o = 20 mW	890	904	910	nm
Beam Divergence	$\theta_{//}$	P_o = 20 mW	7	10	13	°
Beam Divergence	$\theta_{\perp}$	P_o = 20 mW	15	30	35	°
Monitor Current	I_m	P_o = 20 mW	0.6	1	1.2	mA